

SI2301-2.5A

POWER MOSFET

-2.5A, -20V P-CHANNEL ENHANCEMENT MODE POWER MOSFET

DESCRIPTION

The S I 2301 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

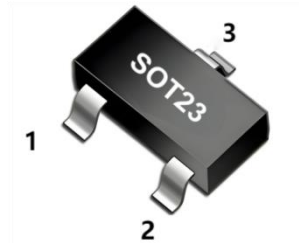
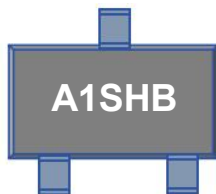
The S I 2301 meet the RoHS and Green Product requirement with full function reliability approved.

FEATURE

- * Green Device Available
- * Super Low Gate Charge
- * Excellent Cdv/dt effect decline
- * Advanced high cell density Trench technology

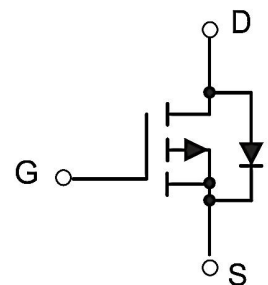
MARKING

Type Code: Marking: A1SHB



1. GATE
2. SOURCE
3. DRAIN

Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS(TA=25°C, unless otherwise specified.)

SYMBOL	PARAMETER	VALUE	UNIT
VDS	Drain-Source Voltage	-20	V
VGS	Gate Source Voltage	±10	V
ID@TA=25°C	Continuous Drain Current, VGS @ -4.5V	-2.5	A
ID@TA=70°C	Continuous Drain Current, VGS @ -4.5V	-1.4	A
IDM	Pulsed Drain Current	-8	A
PD@TA=25°C	Total Power Dissipation	0.4	W
TJ	Storage Temperature	150	°C
TSTG	Thermal Resistance Fr .00m Junction To Ambient	-55~150	°C

THERMAL DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
RθJA	Thermal Resistance Junction-ambient		315	°C/W

■ ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Off Characteristic						
V(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=-250μA	-20			V
IDSS	Zero Gate Voltage Drain Current	VDS=-20V, VGS=0V			-1	μA
IGSS	Gate to Body Leakage Current	VDS=0V, VGS=±12V			±100	nA
On Characteristics						
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=-250μA	-0.4	-0.7	-1.0	V
RDS(on)	Static Drain-Source on-Resistance note2	VGS=-4.5V, ID=-2A		75	115	mΩ
		VGS=-2.5V, ID=-1.5A		135	160	
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-10V, VGS=0V f =1.0MHz		185		pF
Coss	Output Capacitance			35		pF
Crss	Reverse Transfer Capacitance			25		pF
Qg	Total Gate Charge	VDS=-10V, ID=-2A VGS=-4.5V		2.2		nC
Qgs	Gate-Source Charge			0.5		nC
Qgd	Gate-Drain(“Miller”) Charge			0.5		nC
Switching Characteristics						
td(on)	Turn-on Delay Time	VDD=-10V, RL=5Ω RGEN=3Ω,VGS=-4.5V		10		ns
tr	Turn-on Rise Time			30		ns
td(off)	Turn-off Delay Time			63		ns
tf	Turn-off Fall Time			50		ns
Drain-Source Diode Characteristics and Maximum Ratings						
IS	Maximum Continuous Drain to Source Diode Forward Current				-2	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current				-8	A
VSD	Drain to Source Diode Forward Voltage	VGS=0V, IS=-2A			-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

TYPICAL CHARACTERISTICS

Figure1: Output Characteristics

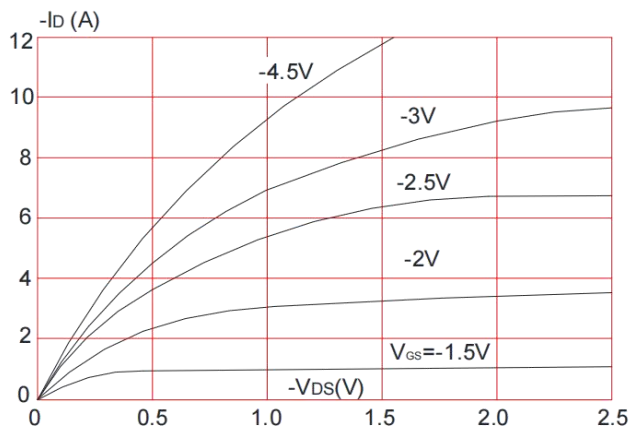


Figure 2: Typical Transfer Characteristics

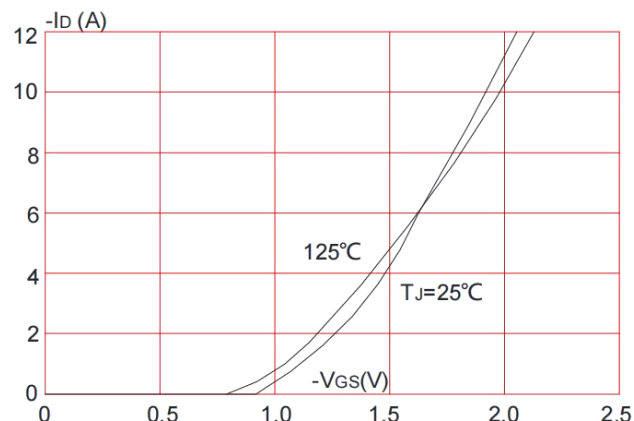


Figure 3: On-resistance vs. Drain Current

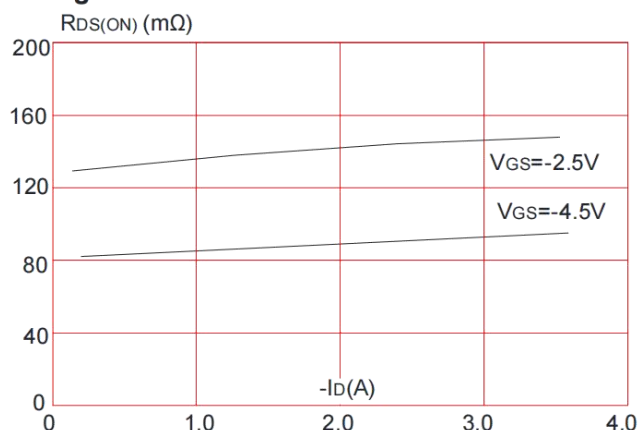


Figure 4: Body Diode Characteristics

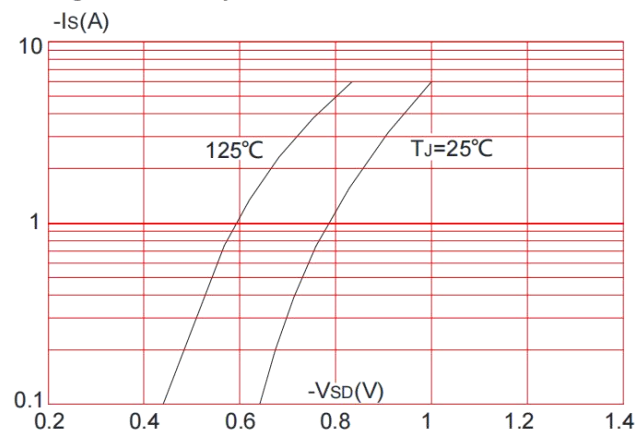


Figure 5: Gate Charge Characteristics

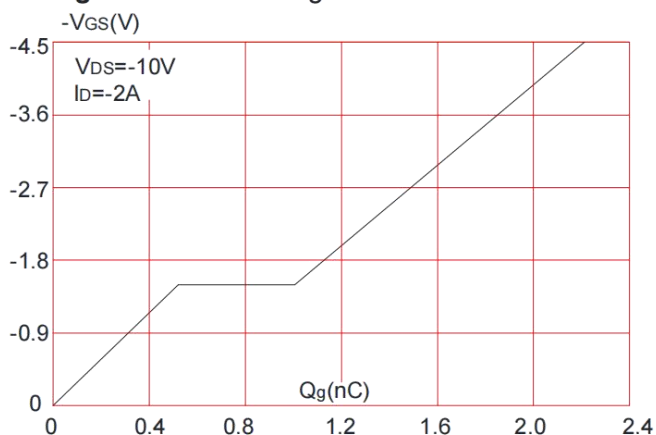
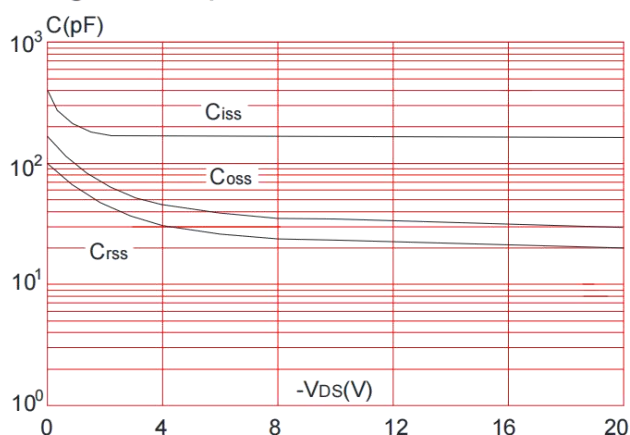


Figure 6: Capacitance Characteristics



TYPICAL CHARACTERISTICS

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

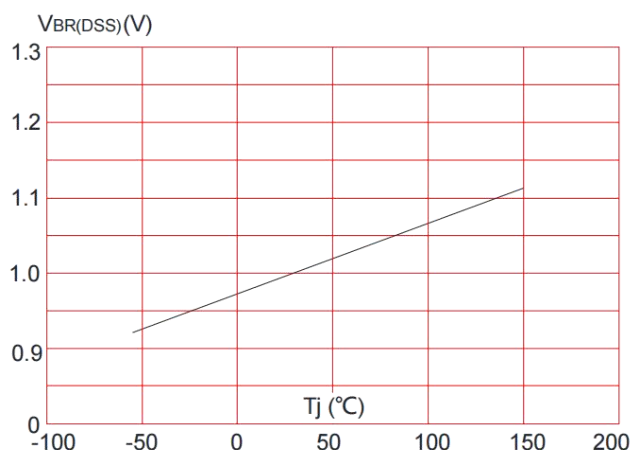


Figure 8: Normalized on Resistance vs. Junction Temperature

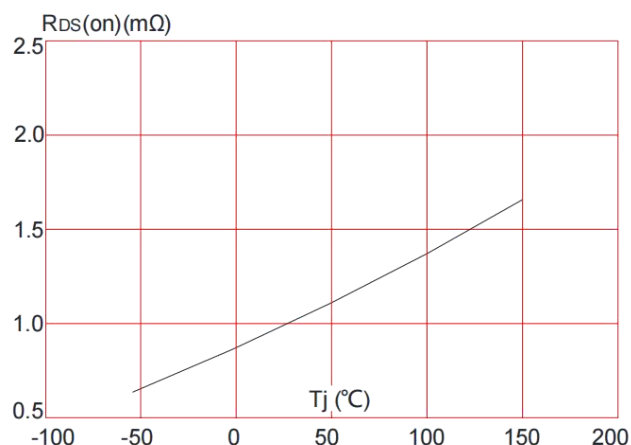


Figure 9: Maximum Safe Operating Area

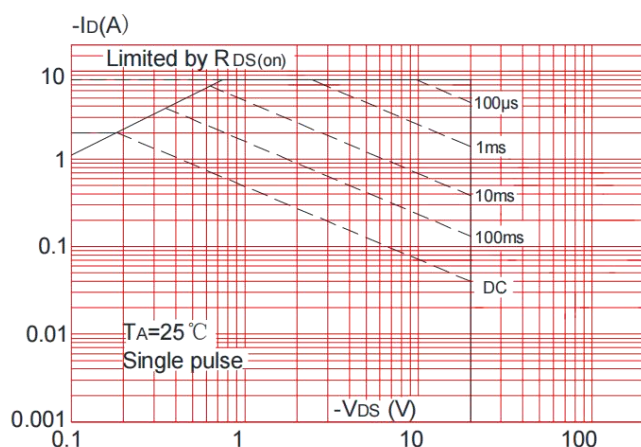


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

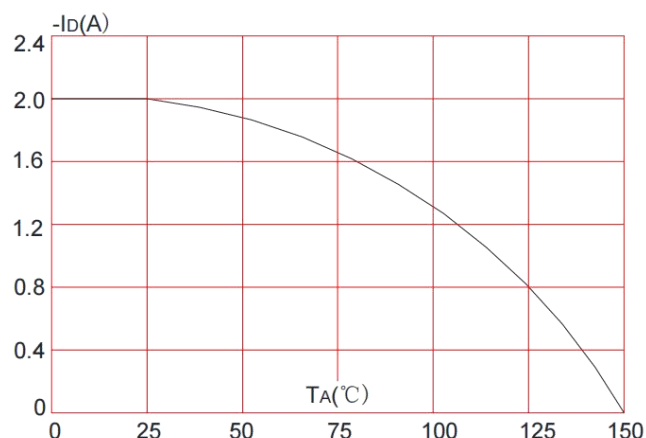
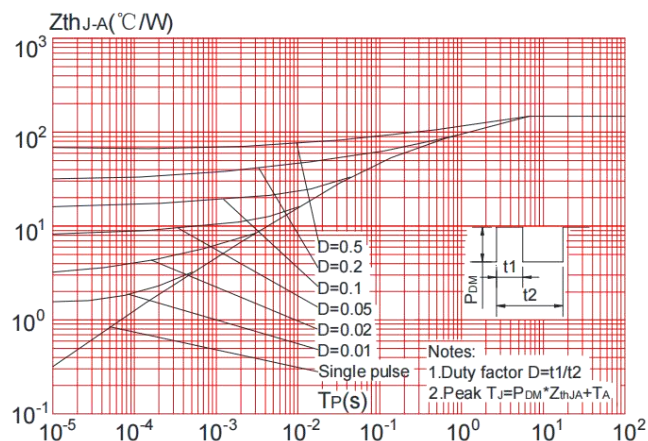
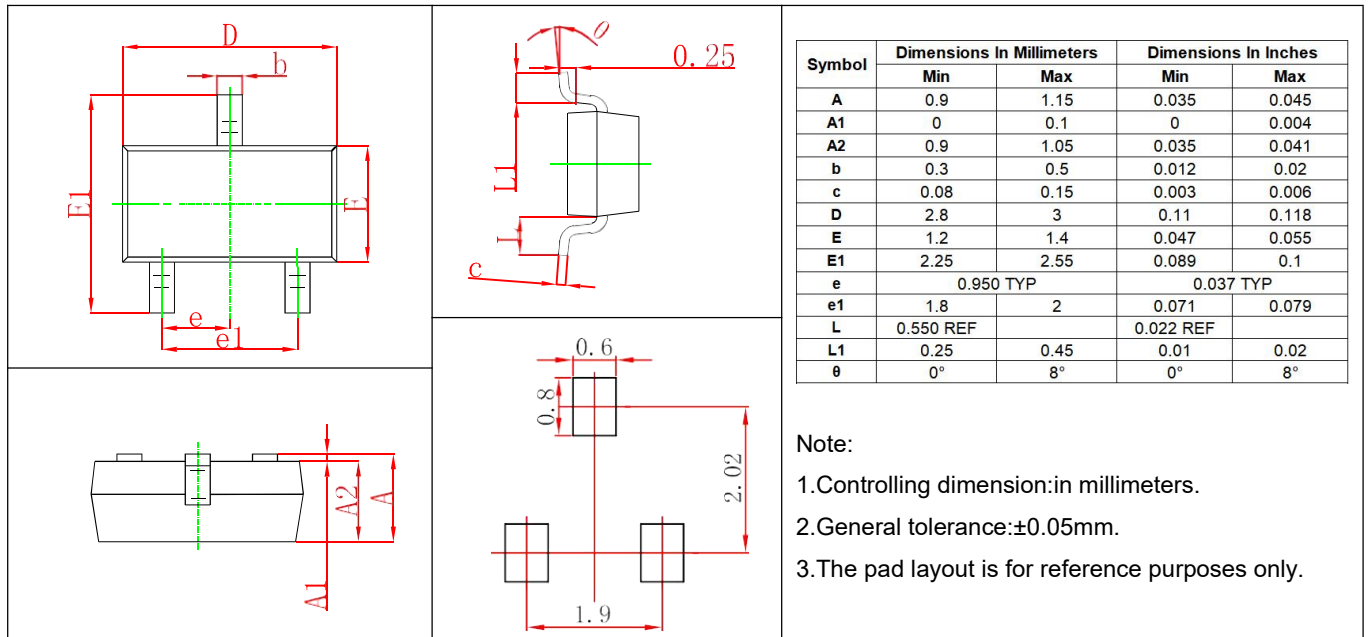


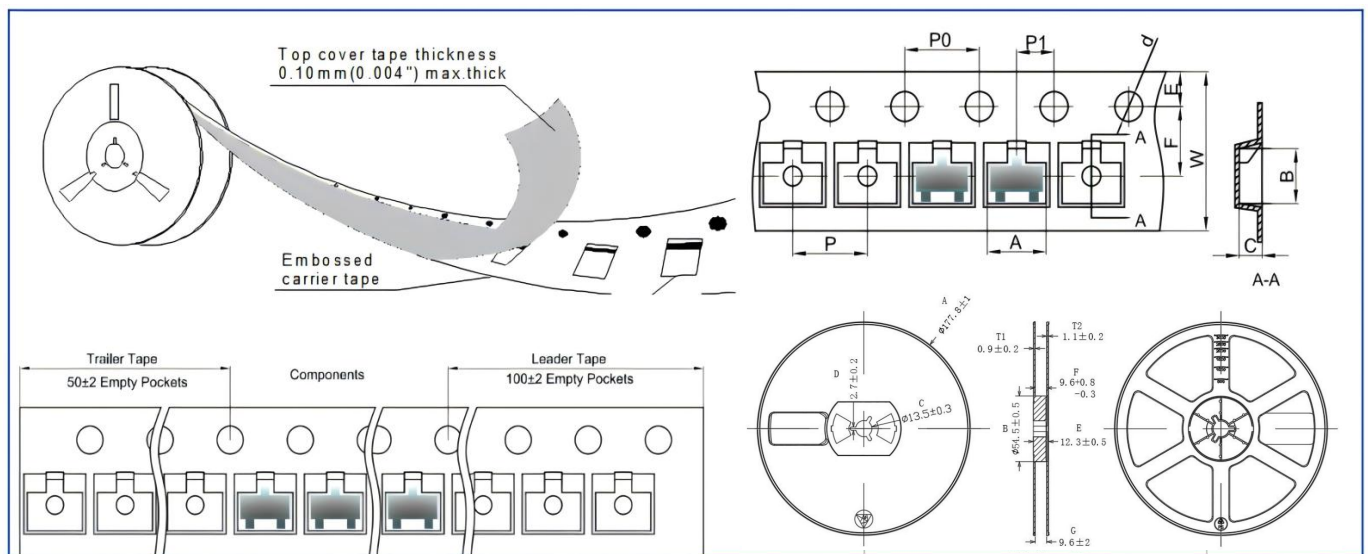
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



■ SOT23 PACKAGE OUTLINE DIMENSIONS



■ REEL PACKING



Dimensions are in millimeter										
PKG TYPE	A	B	C	d	E	F	Po	P	P1	W
SOT-23	3.17	2.77	1.22	Φ1.55	1.75	3.50	4.00	4.00	2.00	8.00
Reel Option	A	B	C	D	E	F	G	T1	T2	Q.TY PER REEL
7" Dia	Φ177.8	Φ54.5	Φ13.5	2.7	12.3	9.6	9.6	0.9	1.1	3000PCS